

Landolt-Börnstein Substance/Property Index

III/41: Semiconductors

(revised and extended contents of the volumes III/17 and III/22)

Subvolume III/41A1: Group IV elements, IV-IV and III-V compounds

General Introduction

List of substances

Group IV elements and IV-IV compounds

[diamond \(C\)](#)

[silicon \(Si\)](#)

[germanium\(Ge\)](#)

[grey tin \(\$\alpha\$ -Sn\)](#)

[silicon carbide \(SiC\)](#)

[silicon-germanium mixed crystals \(\$\text{Si}_x\text{Ge}_{1-x}\$ \)](#)

III-V compounds

[boron nitride \(BN\)](#)

[boron phosphide \(BP\)](#)

[boron arsenide \(BAs\)](#)

[boron antimonide \(BSb\)](#)

[aluminum nitride \(AlN\)](#)

[aluminum phosphide \(AlP\)](#)

[aluminum arsenide \(AlAs\)](#)

[aluminum antimonide \(AlSb\)](#)

[gallium nitride \(GaN\)](#)

[gallium phosphide \(GaP\)](#)

[gallium arsenide \(GaAs\)](#)

[gallium antimonide \(GaSb\)](#)

[indium nitride \(InN\)](#)

[indium phosphide \(InP\)](#)

[indium arsenide \(InAs\)](#)

[indium antimonide \(InSb\)](#)

Solid solutions between III-V compounds

General remarks

[B_xGa_{1-x}N](#)

[B_xGa_{1-x}P](#)

[B_xGa_{1-x}As](#)

[Al_xGa_{1-x}N](#)

[Al_xGa_{1-x}P](#)

[Al_xGa_{1-x}As](#)

[Al_xGa_{1-x}Sb](#)

[Al_xIn_{1-x}P](#)

[Al_xIn_{1-x}As](#)

[Al_xIn_{1-x}Sb](#)

[Ga_xIn_{1-x}N](#)

[Ga_xIn_{1-x}P](#)

[Ga_xIn_{1-x}As](#)

[Ga_xIn_{1-x}Sb](#)

[AlN_xP_{1-x}](#)

[AlAs_{1-x}P_x](#)

[GaN_xP_{1-x}](#)

[GaN_xAs_{1-x}](#)

[GaP_xAs_{1-x}](#)

[GaP_xSb_{1-x}](#)

[GaAs_{1-x}Sb_x](#)

[InP_xAs_{1-x}](#)

[InP_xSb_{1-x}](#)

[InAs_xSb_{1-x}](#)

[InBi_xAs_{1-x}](#)

[InBi_xSb_{1-x}](#)

[In_{1-x}Sb_xAs](#)

Quaternary alloys of the type $\text{III}_x\text{-III}_{1-x}\text{-V}_y\text{-V}_{1-y}$

[General remarks](#)

[Al_x](#) [Ga_{1-x}](#) [As_y](#) [Sb_{1-y}](#)

[Ga_x](#) [In_{1-x}](#) [As_y](#) [P_{1-y}](#)

[Ga_x](#) [In_{1-x}](#) [As_y](#) [Sb_{1-y}](#)

Quaternary alloys of the type $\text{III}_{1-x-y}\text{-III}_x\text{-III}_y\text{-V}$

[Al_x](#) [Ga_y](#) [In_{1-x-y}](#) [P](#)

[Al_x](#) [Ga_y](#) [In_{1-x-y}](#) [As](#)

[Al_x](#) [Ga_y](#) [In_{1-x-y}](#) [Sb](#)

Quaternary alloys of the type $\text{III-V}_{1-x-y}\text{-V}_x\text{-V}_y$

[InAs_{1-x-y}](#) [Sb_y](#) [P_x](#)

Solid solutions between III-V and II-VI compounds

[\(III-V\)_x](#) [\(II-VI\)_{1-x}](#)

Solid solutions between III-V compounds and group IV elements

[\(III-V\)_{1-x}](#) [IV_x](#) or [\(III-V\)_{1-x}](#) [IV_{2x}](#)

Al(x)Ga(1-x)As

[back to top](#)

[band structure, energy gaps](#)

[effective masses, deformation potentials and related parameters](#)

[further band structure parameters](#)

[lattice properties](#)

[optical properties](#)

[thermodynamic and structural data, impurities](#)

[transport properties](#)

Al(x)Ga(1-x)As(y)Sb(1-y)

[back to top](#)

[physical properties](#)

Al(x)Ga(1-x)N

[back to top](#)

[physical data](#)

Al(x)Ga(1-x)P

[back to top](#)

[physical data](#)

Al(x)Ga(1-x)Sb

[back to top](#)

[electronic properties](#)

[further properties](#)

Al(x)In(1-x)As

[back to top](#)

[physical properties](#)

Al(x)In(1-x)P

[back to top](#)

[Ordering effects](#)

[physical properties](#)

Al(x)In(1-x)Sb

[back to top](#)

[physical properties](#)

Aluminum arsenide (AlAs)

[back to top](#)

[bulk modulus](#)

[dielectric constants](#)

[Grüneisen parameters, phonon width and shift, eigenvectors, mean square displacements](#)

[internal strain, effective charges](#)

[lattice parameters, thermal expansion](#)

[phase transition parameters](#)

[phonon dispersion, phonon wavenumbers and frequencies](#)
[piezoelectric parameters, second- and third-order susceptibilities](#)
[sound velocities, elastic moduli](#)
[structure](#)
[band structure](#)
[band structure parameters, deformation potentials](#)
[camel's back structure of the conduction band at X:](#)
[carrier mobilities, Seebeck coefficient](#)
[crystal structure, lattice parameters, thermal expansion](#)
[Debye temperature, hardness, density, melting point](#)
[effective masses](#)
[elastic moduli, compliances and derived parameters](#)
[electrical and thermal conductivity, carrier concentration](#)
[energies of symmetry points of the band structure](#)
[energy gaps](#)
[exciton binding energy](#)
[impurities and defects](#)
[intra- and interband transition energies, spin-orbit splitting](#)
[optical properties, refractive index, dielectric constants](#)
[phonon dispersion, phonon wavenumbers](#)
[sound velocities](#)
[thermodynamical parameters](#)

AlAs(1-x)P(x)

[back to top](#)

[physical properties](#)

Aluminum nitride (AlN)

[back to top](#)

[bulk modulus, Young's and shear modulus](#)
[dielectric constants](#)
[Grüneisen parameters, phonon line width and shift](#)
[internal strain, effective charges, spontaneous polarization](#)
[lattice parameters](#)
[phase diagram, equation of state, phase transition parameters](#)
[phonon dispersion curves, density of state](#)
[phonon eigenvectors, mean square displacements](#)
[phonon spectra, phonon wavenumbers](#)
[piezoelectric constants, electromechanical coupling factor](#)
[second- and third-order susceptibilities](#)
[sound velocities, elastic moduli](#)
[specific heat, thermal conductivity](#)
[structure](#)
[thermal expansion](#)
[third-order elastic constants](#)
[band structure](#)
[crystal structure, lattice parameters, thermal expansion](#)

[Debye temperature, density, hardness, melting point](#)
[effective masses, valence band parameters](#)
[effective masses, valence band parameters of the zincblende modification](#)
[elastic moduli, bulk modulus](#)
[electrical and thermal conductivity](#)
[energies of symmetry points of the band structure, critical point energies](#)
[energy gap](#)
[hole mobility, piezoelectric strain coefficients](#)
[interband trans. energies, def. potentials, crystal field, spin-orbit splitting](#)
[optical properties, dielectric constants, refractive index](#)
[phonon dispersion and wavenumbers, Grüneisen parameters, eff. charge](#)
[thermodynamical parameters, vaporization](#)

AlN(x)P(1-x)

[back to top](#)

[physical properties](#)

Aluminum phosphide (AlP)

[back to top](#)

[bulk modulus](#)
[dielectric constants](#)
[elastic moduli](#)
[internal strain, effective charges](#)
[lattice parameters, thermal expansion](#)
[phonon dispersion, phonon frequencies, Grüneisen parameters](#)
[piezoelectric parameters, second- and third-order susceptibilities](#)
[structure, phase transitions](#)
[band gaps](#)
[band structure, energies of symmetry points](#)
[crystal structure, transition pressures](#)
[Debye temperature, density, melting point](#)
[effective masses](#)
[elastic moduli, bulk modulus](#)
[electrical and thermal transport](#)
[impurities and defects](#)
[lattice parameter](#)
[optical properties, dielectric constants](#)
[parameters of valence band](#)
[phonon dispersion, phonon wavenumbers](#)
[thermodynamical parameters, vaporization](#)

Grey tin (alpha-Sn)

[back to top](#)

[bulk and shear modulus](#)
[Debye-Waller factor](#)
[elastic moduli](#)
[high-frequency dielectric constant](#)
[internal-strain parameter](#)

[lattice parameters](#)
[phase transition pressure and volume change](#)
[phonon dispersion curves, density of states](#)
[phonon frequencies and wavenumbers and related parameters](#)
[structure, phase diagram, equation of state](#)
[thermal expansion](#)
[anisotropy parameters, g-factor of light electrons](#)
[band structure](#)
[critical point energies](#)
[crystal structure, lattice parameter \(pure Sn, Sn-IV alloys\), thermal expansion](#)
[Debye temperature, density, bulk modulus, heat capacity](#)
[effective masses](#)
[energies of symmetry points of the band structure](#)
[impurities and defects](#)
[interband transition energies](#)
[intraband transition energies](#)
[Luttinger parameters, deformation potentials](#)
[magnetic properties](#)
[optical properties, dielectric constant](#)
[phonon frequencies, elastic moduli](#)
[transport properties](#)

Aluminum antimonide (AlSb)

[back to top](#)

[bulk modulus](#)
[dielectric constants](#)
[Grüneisen parameters, phonon line width, phonon eigenvectors, mean square displacements](#)
[internal strain, effective charges](#)
[lattice parameters, thermal expansion](#)
[phonon dispersion, phonon wavenumbers](#)
[piezoelectric constants, second- and third-order susceptibilities](#)
[sound velocities, elastic moduli](#)
[structure, phase transitions](#)
[band structure, energies of symmetry points](#)
[carrier concentration, Hall scattering factor](#)
[conduction band, camel's back structure and effective masses](#)
[conduction band, effective masses](#)
[core level energies](#)
[critical point energies](#)
[crystal structure of various phases](#)
[Debye temperature, density, hardness, melting point](#)
[deformation potentials](#)
[elastic moduli, bulk modulus](#)
[electrical and thermal conductivity](#)
[electron loss, photoelectric threshold](#)
[electron mobility](#)
[energy gaps](#)

[exciton binding energy](#)
[further valence band parameter](#)
[Grüneisen parameters, effective charge](#)
[hole mobility](#)
[impurities and defects](#)
[lattice parameter, thermal expansion](#)
[magnetoresistance](#)
[optical properties, dielectric constants](#)
[phonon dispersion, phonon wavenumbers and energies](#)
[piezo- and elasto-resistance](#)
[piezoelectric coefficients](#)
[piezooptic and further optical parameters](#)
[Seebeck and Nernst coefficient](#)
[sound velocities](#)
[spin-orbit splitting energies](#)
[thermodynamical parameters, vaporization](#)
[transitions involving core levels](#)
[transport parameters near the melting temperature](#)
[valence band, effective masses](#)

B(x)Ga(1-x)As

[back to top](#)

[physical data](#)

B(x)Ga(1-x)N

[back to top](#)

[physical data](#)

B(x)Ga(1-x)P

[back to top](#)

[physical data](#)

Boron arsenide (BAs)

[back to top](#)

[elastic moduli, bulk modulus](#)
[internal strain, effective charge, dielectric constant, third-order susceptibility](#)
[lattice parameters, thermal expansion](#)
[phonon dispersion, phonon wavenumbers](#)
[structure, phase transitions](#)
[band structure](#)
[crystal structure, density, Debye temperature](#)
[thermodynamical data](#)

Boron nitride (BN)

[back to top](#)

[bulk modulus](#)
[dielectric constants](#)
[effective charges](#)

[elastic moduli](#)
[Grüneisen parameters, phonon line width, mean square displacements](#)
[heat capacity, shock wave velocities](#)
[lattice parameters](#)
[linear thermal expansion, temperature dependence of lattice parameters](#)
[phase diagram, equation of state](#)
[phase transition data](#)
[phonon dispersion curves and density of states](#)
[phonon wavenumbers and frequencies](#)
[piezoelectric parameters, third order susceptibility](#)
[structure](#)
[Young's modulus, internal strain](#)
[band structure, hexagonal modification](#)
[Debye temperature, heat capacity, density a. rel. parameters, hex. modification](#)
[deformation potentials, cubic modification](#)
[effective masses, electron affinity, cubic modification](#)
[energy gap, effective masses, hexagonal modification](#)
[energy gap, width of valence band and related data, cubic modification](#)
[general remarks and band structure, cubic modification](#)
[interband and core state transition energies, hexagonal modification](#)
[lattice parameters, cubic modification](#)
[melting point, Debye temperature density, entropy, etc., cubic modification](#)
[normal pressure and high pressure phases](#)
[optical properties, dielectric constant, cubic modification](#)
[optical properties, dielectric constants, hexagonal modification](#)
[phonon frequencies, elastic constants and related properties, hex. modification](#)
[phonon wavenumbers, elastic and related parameters, cubic modification](#)
[properties of rhombohedral BN](#)
[properties of wurtzite-type BN](#)
[structure of valence band, hexagonal modification](#)
[structure, lattice parameter, thermal expansion, hexagonal modification](#)
[thermodynamic parameters, vaporization, hexagonal modification](#)
[transport properties, cubic modification](#)
[transport properties, hexagonal modification](#)

Boron phosphide (BP)

[back to top](#)

[bulk modulus](#)
[dielectric constants](#)
[elastic moduli](#)
[Grüneisen parameters, phonon eigenvectors, mean square displacements](#)
[internal strain, effective charges](#)
[lattice parameters](#)
[linear thermal expansion coefficient](#)
[phonon dispersion, wavenumbers and frequencies](#)
[piezoelectric constant, third-order susceptibility](#)
[structure, equation of state, specific heat, phase transitions](#)

[band structure, energy gap](#)
[crystal structure, lattice parameters, thermal expansion](#)
[Debye temperature, melting point, hardness](#)
[deformation potentials](#)
[elastic moduli, bulk a. shear modulus, mode Grüneisen param., eff. charge](#)
[electrical and thermal conductivity](#)
[further transport properties](#)
[higher energy optical transitions](#)
[impurities and defects](#)
[optical properties, dielectric constant](#)
[phonon energies and wavenumbers](#)
[thermodynamical properties](#)

Boron antimonide (BSb)

[back to top](#)

[lattice parameters, phonon dispersion relation, phonon eigenvectors, bulk modulus](#)
[physical properties](#)

Diamond (C)

[back to top](#)

[bulk modulus](#)
[critical-point frequencies](#)
[elastic moduli](#)
[electric field, pressure and strain dependences of phonon frequencies](#)
[fourth-order elastic constants](#)
[fourth-order phonoelastic constants](#)
[Grüneisen parameters](#)
[high-frequency dielectric constant](#)
[internal strain](#)
[isotope dependence of lattice frequencies](#)
[isotope dependence of the phonon density of states and of two-phonon spectra](#)
[lattice parameters](#)
[linear thermal expansion coefficient](#)
[non-linear optical coefficients](#)
[phase diagram, equation of state](#)
[phase transition pressure, volume change](#)
[phonon dispersion relations, phonon density of states](#)
[phonon eigenvectors, mean square displacement, isotope effect of sound velocities](#)
[phonon wave numbers and frequencies](#)
[phonon wavenumbers and frequencies](#)
[pressure, strain and isotope dependence of phonon width](#)
[Raman frequencies, temperature dependence and frequency shift](#)
[structure](#)
[temperature dependence of phonon self energy, frequency dependence of the damping function](#)
[third-order elastic constants](#)
[third-order phonoelastic constants](#)
[two-phonon density of states and second-order Raman and infrared spectra](#)

[zone-center Raman phonon linewidth](#)

[band structure](#)

[Debye temperature, heat capacity, density, hardness, melting point and related data](#)

[deformation potentials, electron-hole drop parameters](#)

[effective masses](#)

[elastic moduli](#)

[elastooptic constants, further optical properties](#)

[electrical and thermal conduction, transport properties](#)

[energies of symmetry points of the band structure](#)

[energy gaps](#)

[exciton binding energy](#)

[general characterization](#)

[g-factor, valence band parameters](#)

[Grüneisen parameters, Poissons ratio, bulk modulus](#)

[lattice parameters, thermal expansion](#)

[magnetic properties](#)

[normal pressure and high pressure phases](#)

[phonon dispersion, phonon frequencies](#)

[refractive index, dielectric constants](#)

[sound velocity](#)

[spin-orbit splitting, interband transition energies](#)

Ga(x)In(1-x)As

[back to top](#)

[Ordering effects](#)

[physical properties](#)

Ga(x)In(1-x)As(y)P(1-y)

[back to top](#)

[physical properties](#)

Ga(x)In(1-x)As(y)Sb(1-y)

[back to top](#)

[physical properties](#)

Ga(x)In(1-x)N

[back to top](#)

[physical properties](#)

Ga(x)In(1-x)P

[back to top](#)

[electronic properties](#)

[further properties](#)

[Ordering effects](#)

Ga(x)In(1-x)Sb

[back to top](#)

[physical properties](#)

Gallium arsenide (GaAs)

[back to top](#)

[bulk modulus, Young's and torsional modulus](#)

[dielectric constants](#)

[Grüneisen parameters, phonon line shift and width](#)

[internal strain, effective charges](#)

[lattice parameters, thermal expansion](#)

[phase transition parameters](#)

[phonon dispersion, phonon spectra](#)

[phonon lifetime, phonon eigenvectors, mean square displacements](#)

[phonon wavenumbers and frequencies](#)

[piezoelectric and elastooptic parameters, second- and third-order susceptibilities](#)

[second- and third-order elastic moduli and compliances](#)

[sound velocities, ultrasonic attenuation, phonon viscosity](#)

[structure, phase diagram, equation of state](#)

[absorption spectrum in the vacuum uv](#)

[Auger effect](#)

[band structure](#)

[bulk, Young's and torsion moduli, internal strain](#)

[camel's back structure of X6 conduction band minimum](#)

[conduction band effective masses and related parameters](#)

[core level binding energies, photoionization cross-sections](#)

[core level energies](#)

[crystal structure, phases](#)

[data from electron loss, yield and X-ray emission spectroscopy](#)

[data from photoelectron spectroscopy \(ESCA\)](#)

[data from Raman spectra](#)

[Debye temperature, density, heat capacity, melting point](#)

[deformation potentials](#)

[dielectric constants](#)

[direct energy gap](#)

[elastic moduli](#)

[elastoresistance coefficients](#)

[electron drift velocity and diffusion coefficient](#)

[electron mobility](#)

[electron-two-phonon deformation potentials](#)

[electrooptic constants, second and third order nonlinear susceptibilities](#)

[energies of symmetry points of the band structure](#)

[exciton ground and excited states](#)

[further optical spectra](#)

[Grüneisen parameters, effective charge](#)

[Hall scattering factor](#)

[hole mobility and drift velocity](#)

[indirect energy gap](#)

[interband transition energies \(critical point energies\)](#)

[intra- and interband transition energies](#)

[intrinsic carrier concentration, electrical and thermal conductivity](#)

[lattice parameter, thermal expansion](#)

[magnetic properties](#)
[magnetoresistance](#)
[minority carrier transp., impact ioniz., carrier lifetimes, plasmon energy](#)
[Nernst coefficient](#)
[non-parabolicity and warping parameters](#)
[optical constants](#)
[other parameters related to conduction band minima, g-factors](#)
[phonon dispersion, phonon frequencies and wavenumbers](#)
[photoemission data](#)
[piezoelectric constants](#)
[piezooptic constants, piezobirefringence](#)
[piezoresistance tensor coefficients](#)
[reflectance, two-photon absorption](#)
[refractive index, absorption index, absorption coefficients](#)
[Schottky barriers](#)
[Seebeck coefficient](#)
[sound velocities](#)
[spin-orbit splitting energies](#)
[thermodynamical parameters, vaporization](#)
[third order elastic moduli](#)
[transport mechanisms](#)
[typical data for semi-insulating GaAs](#)
[valence band parameters](#)
[valence bands, effective masses](#)

GaAs(1-x)Sb(x)

[back to top](#)

[physical properties](#)

Gallium nitride (GaN)

[back to top](#)

[bulk modulus](#)
[dielectric constants](#)
[elastic moduli](#)
[Grüneisen parameters](#)
[internal strain, effective charges, spontaneous polarization](#)
[lattice parameters, thermal expansion](#)
[mean square displacements, sound velocities](#)
[phase diagram, equation of states, phase transitions](#)
[phonon dispersion, density of states, Raman and infrared spectra](#)
[phonon wavenumbers and frequencies](#)
[phonon width and shift, phonon eigenvectors](#)
[piezoelectric constants](#)
[second and third order susceptibilities](#)
[structure](#)
[band structure](#)
[crystal structure, lattice param., thermal expansion, high pressure phases](#)

[Debye temperature, melting point, density](#)
[effective masses, g-factors, deformation potentials](#)
[electrical and thermal conductivity, electron concentration](#)
[energy gap, exciton binding energy](#)
[interband transition and splitting energies](#)
[magnetic properties](#)
[mobilities, Seebeck effect](#)
[optical properties, dielectric constant](#)
[phonon data, elastic moduli, Grüneisen and rel. parameters](#)
[thermodynamical parameters, vaporization](#)

GaN(x)As(1-x)

[back to top](#)

[physical properties](#)

GaN(x)P(1-x)

[back to top](#)

[physical properties](#)

Gallium phosphide (GaP)

[back to top](#)

[bulk modulus, Young's and torsional modulus](#)
[dielectric constants](#)
[Grüneisen parameters, phonon eigenvectors, mean square displacements](#)
[internal strain, effective charges](#)
[lattice parameters, thermal expansion](#)
[phase transition parameters](#)
[phonon dispersion, density of states](#)
[phonon frequencies and wavenumbers](#)
[phonon self energy, phonon line shift and width](#)
[piezoelectric and electrooptic parameters, second- and third-order susceptibility](#)
[sound velocities, second- and third-order elastic moduli](#)
[structure, equation of state, specific heat](#)
[band structure](#)
[bulk modulus, mode Grüneisen parameters and related data](#)
[camel's back structure of conduction band, effective masses](#)
[conduction and valence band, effective masses](#)
[critical points of phonon dispersion curves](#)
[crystal structure of various phases](#)
[data from angle integrated photoemission](#)
[Debye temperature, density, hardness, heat capacity](#)
[deformation potentials](#)
[direct energy gap](#)
[elastic moduli](#)
[electron concentration and mobility](#)
[energies of symmetry points of the band structure](#)
[energy gaps, temperature and pressure dependence](#)
[exciton ground state](#)

[further optical properties](#)
[hole concentration and mobility](#)
[indirect band gaps](#)
[interband transition and splitting energies](#)
[lattice parameter, thermal expansion, Grüneisen parameters](#)
[magnetic properties](#)
[magnetoresistance, Seebeck coefficient](#)
[minority carrier and positron lifetimes, plasmon energy](#)
[optical constants](#)
[optical properties involving core level transitions](#)
[phonon dispersion, phonon frequencies](#)
[piezoelectric coefficients](#)
[pressure dependence of elastic moduli](#)
[refractive index, absorption, reflection, dielectric constants](#)
[second order nonlin. dielectric susceptibilities, birefringence, etc.](#)
[sound velocities](#)
[thermodynamical data, vaporization](#)
[third order elastic moduli](#)
[transport mechanisms, electrical and thermal conductivity](#)
[transverse effective charge](#)
[valence band parameters](#)
[Young's moduli and torsional modulus](#)

GaP(x)As(1-x)

[back to top](#)

[physical properties](#)

GaP(x)Sb(1-x)

[back to top](#)

[physical properties](#)

Gallium antimonide (GaSb)

[back to top](#)

[bulk modulus, Young's and shear modulus](#)
[dielectric constants](#)
[elastic moduli](#)
[Grüneisen parameters, phonon line width and eigenvectors, mean square displacements](#)
[internal strain, effective charges](#)
[lattice parameters, thermal expansion](#)
[phase diagram, equation of state, phase transitions](#)
[phonon dispersion, wavenumbers and frequencies](#)
[piezoelectric parameters, second- and third-order susceptibilities](#)
[sound velocity, ultrasonic attenuation](#)
[structure](#)
[absorption spectrum in the vacuum uv](#)
[Auger coefficient](#)
[band structure, energies of symmetry points](#)
[bulk modulus](#)

[conduction band splitting by strain](#)
[conduction band, effective masses](#)
[critical point effective mass, spin-orbit splitting valence band](#)
[critical point energies](#)
[crystal structure, high-pressure phases](#)
[data for the L and X conduction band minima](#)
[data from angle integrated photoemission](#)
[Debye temperature, density, hardness, melting point](#)
[deformation potentials](#)
[dielectric constants](#)
[direct energy gap](#)
[effective charge](#)
[elastic moduli](#)
[elastoresistance coefficients](#)
[electron loss and yield spectroscopy](#)
[electron mobility](#)
[exciton ground state](#)
[Hall scattering factor](#)
[heavy and light hole mobilities](#)
[higher band-band transitions \(critical point energies\)](#)
[higher conduction band minima, energy difference to lowest minimum](#)
[hole mobility](#)
[intrinsic carrier concentration, resistivity](#)
[lattice parameter, thermal expansion](#)
[magnetic properties](#)
[magnetoresistance](#)
[mode Grüneisen parameters](#)
[Nernst coefficient](#)
[optical properties, optical constants](#)
[phonon dispersion, phonon frequencies](#)
[photoel. threshold, core levels, photoionization cross section](#)
[piezooptic constants, dependence of phonons on uniaxial stress](#)
[piezoresistance tensor coefficients](#)
[refractive index, absorption index and coefficient](#)
[Schottky barriers](#)
[second order nonlinear dielectric susceptibilities](#)
[Seebeck coefficient](#)
[spin-orbit splitting energies](#)
[structure of conduction band minimum and valence band maximum](#)
[thermal conductivity](#)
[thermodynamical parameters](#)
[third order elastic moduli](#)
[transport mechanisms](#)
[valence band parameters](#)
[valence band, effective masses](#)

Germanium (Ge)

[back to top](#)

[bulk modulus](#)

[elastic moduli](#)

[high-frequency dielectric constant](#)

[internal strain](#)

[lattice parameters](#)

[mean square displacements](#)

[mode Grüneisen parameters](#)

[phase diagram, equation of state](#)

[phase transition pressure and volume change](#)

[phonon dispersion relations, density of states](#)

[phonon shift and width](#)

[phonon wavenumbers and frequencies](#)

[photoelasticity](#)

[Raman phonon frequencies and wavenumbers](#)

[sound velocities, ultrasound attenuation](#)

[structure](#)

[thermal expansion](#)

[third-order elastic moduli](#)

[third-order susceptibility](#)

[band structure](#)

[conduction band, effective masses](#)

[critical point energies](#)

[crystal structure of the various modifications](#)

[data from Raman measurements](#)

[Debye temperature, density, hardness, melting point, heat capacity](#)

[deformation potentials](#)

[dielectric constant](#)

[direct and optical energy gap](#)

[effective number of free electrons](#)

[elastic moduli](#)

[elastoresistance coefficients](#)

[electron mobility](#)

[electrostriction coefficients](#)

[energies of symmetry points of the band structure](#)

[energy of phonon modes in amorphous samples](#)

[exciton data](#)

[g-factor of electrons](#)

[g-factor, spin-orbit split-off band](#)

[Hall scattering factor](#)

[heats of fusion and sublimation, enthalpy and entropy, vapor pressure](#)

[higher band-band transitions \(critical point energies\)](#)

[hole mobility](#)

[indirect energy gap](#)

[intrinsic carrier concentration](#)

[lattice parameter, thermal expansion](#)

[magnetic properties](#)

[magnetoresistance](#)
[optical constants](#)
[optical properties involving core level transitions](#)
[optical spectra](#)
[phonon dispersion, phonon frequencies](#)
[phonons participating in indirect transitions](#)
[piezooptic and elastooptic constants, birefringence](#)
[piezoresistance coefficients](#)
[plasma energy of valence electrons](#)
[positron lifetime in Ge](#)
[reduced interband masses at critical point transitions](#)
[refractive index](#)
[Schottky barrier heights](#)
[Seebeck and Nernst coefficients](#)
[sound velocities](#)
[spin-orbit splitting energies](#)
[stopping power for electron energy loss](#)
[strain and field dependence of hole mobility](#)
[thermal conductivity](#)
[third order elastic moduli](#)
[third order susceptibilities](#)
[transport mechanisms, conductivity](#)
[transport properties in liquid Ge](#)
[valence band parameters](#)
[valence band, effective masses](#)
[warm electrons, electron drift velocity](#)
[Young's, torsion and bulk moduli, Grüneisen parameters](#)

In(1-x)Sb(x)As

[back to top](#)

[Ordering effects](#)

In(1-x-y)Al(x)Ga(y)As

[back to top](#)

[physical properties](#)

In(1-x-y)Al(x)Ga(y)P

[back to top](#)

[physical properties](#)

In(1-x-y)Al(x)Ga(y)Sb

[back to top](#)

[physical properties](#)

Indium arsenide (InAs)

[back to top](#)

[bulk modulus](#)

[dielectric constants](#)

[elastic moduli and compliances](#)
[internal strain, effective charges](#)
[lattice parameters, thermal expansion](#)
[phonon dispersion, phonon spectra, phonon wavenumbers](#)
[phonon line width and eigenvectors, Grüneisen parameters, mean square displacements](#)
[piezoelectric parameters, nonlinear susceptibilities](#)
[sound velocities and attenuation](#)
[structure, phase transition parameters](#)
[absorption spectra in the vacuum uv](#)
[band structure, energies of symmetry points](#)
[carrier concentrations](#)
[carrier mobilities, Hall scattering factor](#)
[conduction band, effective masses](#)
[crystal structure, high pressure phases](#)
[data from angle integrated photoemission](#)
[data from Raman spectroscopy](#)
[Debye temperature, density, hardness, melting point](#)
[deformation potentials](#)
[dependence of phonons on uniaxial stress](#)
[dielectric constants](#)
[elastic moduli](#)
[electrical and thermal transport](#)
[electron g-factor, camel's back structure at conduction band edge](#)
[electron loss, yield and X-ray emission spectroscopy](#)
[energy gap, exciton data](#)
[higher band-band transitions](#)
[lattice parameter, thermal expansion](#)
[magnetic properties](#)
[magnetoresistance](#)
[mode Grüneisen parameters, effective charge](#)
[Nernst and Righi-Leduc coefficients](#)
[optical constants](#)
[phonon dispersion, phonon wavenumbers](#)
[photoelectric threshold, binding energies of core levels](#)
[piezooptic constants, piezobirefringence](#)
[piezoresistance and piezoelectric constants](#)
[recombination and generation, lifetimes](#)
[refractive and absorption index, reflectance](#)
[second order nonlinear dielectric susceptibility](#)
[Seebeck coefficient](#)
[sound velocities](#)
[spin-orbit splitting energies](#)
[thermodynamical parameters, vaporization](#)
[valence band parameters](#)
[valence band, effective masses](#)

InAs(1-x-y)Sb(y)P(x)

[back to top](#)

[physical properties](#)

InAs(x)Sb(1-x)

[back to top](#)

[physical properties](#)

InBi(x)As(1-x)

[back to top](#)

[physical properties](#)

InBi(x)Sb(1-x)

[back to top](#)

[physical properties](#)

Indium nitride (InN)

[back to top](#)

[bulk modulus](#)

[dielectric constants](#)

[elastic moduli](#)

[Grüneisen parameters, phonon line width](#)

[internal strain, effective charges, spontaneous polarization](#)

[lattice parameters, thermal expansion](#)

[phonon dispersion, phonon wavenumbers and frequencies](#)

[piezoelectric parameters, third-order susceptibility](#)

[structure, phase transitions](#)

[density, melting point, thermodynamical parameters, vaporization](#)

[electronic properties](#)

[lattice properties](#)

[magnetic properties](#)

[optical properties, dielectric constants](#)

[transport properties](#)

Indium phosphide (InP)

[back to top](#)

[bulk modulus](#)

[dielectric constants](#)

[Grüneisen constants, phonon eigenvector, mean square displacements](#)

[lattice parameters, thermal expansion](#)

[phonon dispersion and density of states, phonon-plasmon modes](#)

[phonon frequencies and wavenumbers](#)

[piezoelectric parameters, second- and third-order susceptibilities](#)

[shear moduli, internal strain, effective charges](#)

[sound velocities, elastic moduli](#)

[structure, phase transition parameters](#)

[absorption spectrum in the vacuum uv](#)

[band structure, energies of symmetry points](#)

[bulk and shear moduli](#)

[conduction band, effective mass](#)

[crystal structure, high pressure phases](#)
[data from angle integrated photoemission and Auger spectra](#)
[data from Raman spectroscopy](#)
[Debye temperature, density, hardness](#)
[deformation potentials](#)
[dielectric constants](#)
[elastic moduli](#)
[electrical and thermal conductivity, carrier concentrations](#)
[electron drift velocity, impact ionization rates](#)
[electron g-factor](#)
[electron mobility](#)
[electron-two-phonon deformation potential](#)
[energy gap](#)
[exciton states and parameters](#)
[Grüneisen constant and parameters](#)
[Hall scattering factor, magnetoresistance](#)
[hole and positron lifetimes, plasmon dispersion](#)
[hole mobility](#)
[interband transition and splitting energies](#)
[intraband transition energies](#)
[lattice parameter, thermal expansion](#)
[magnetic properties](#)
[optical constants](#)
[phonon dispersion and frequencies](#)
[piezooptic constants, piezobirefringence](#)
[piezoresistance tensor coefficient](#)
[pressure dependence of dynamical parameters](#)
[refractive and absorption index, reflectance](#)
[Schottky barrier heights](#)
[second order nonlinear dielectric susceptibilities](#)
[Seebeck and Nernst coefficients](#)
[sound velocities](#)
[temperature, pressure and concentration dependence of energy gaps](#)
[thermodynamical parameters, vaporization](#)
[third order elastic moduli](#)
[transport mechanism](#)
[transverse effective charge](#)
[valence band parameters](#)
[valence band, effective masses](#)
[X-ray emission, photoelectric threshold, binding energies of core levels](#)

InP(x)As(1-x)

[physical properties](#)

[back to top](#)

InP(x)Sb(1-x)

[physical properties](#)

[back to top](#)

Indium antimonide (InSb)

[back to top](#)

[bulk modulus](#)

[dielectric constants](#)

[elastic moduli and compliances](#)

[electromech. coupling coeff., piezoelectric parameters, second- and third-order susceptibility](#)

[Grüneisen parameters, internal strain, effective charges](#)

[Grüneisen parameters, phonon line width and shift, eigenvectors, mean square displacements](#)

[lattice parameters, thermal expansion](#)

[phase transitions](#)

[phonon dispersion, phonon wavenumbers and frequencies](#)

[sound velocity, sound attenuation, phonon viscosity](#)

[structure](#)

[absorption spectra in the vacuum uv](#)

[band structure](#)

[broadening parameters at crit. points, press. and temperature coeff.](#)

[bulk modulus](#)

[carrier concentrations](#)

[conduction band, effective masses](#)

[crystal structure, high pressure phases](#)

[data from angle resolved photoemission](#)

[data from Raman spectroscopy](#)

[Debye temperature, density, hardness, melting point](#)

[deformation potentials](#)

[dielectric constants](#)

[effective mass and g-value at critical points](#)

[elastic moduli](#)

[elastoresistance coefficients](#)

[electrical and thermal transport](#)

[electromechanical coupling coefficient](#)

[electron g-factor](#)

[electron loss, yield and X-ray emission spectroscopy](#)

[electron mobility](#)

[energies of symmetry points of the band structure](#)

[energy gap](#)

[exciton ground state](#)

[Hall scattering factor](#)

[higher band-band transitions](#)

[hole mobility](#)

[impact ionization and recombination rates, Auger recombination](#)

[lattice parameter, thermal expansion](#)

[magnetic properties](#)

[magnetoresistance, piezoresistance](#)

[mode Grüneisen parameters, effective charge](#)

[Nernst, Righi-Leduc and Ettinghausen coefficients](#)

[optical constants](#)

[phonon dispersion and frequencies](#)

[photoelectric threshold, binding energy of core levels](#)

[piezoelectric constants](#)
[piezooptic constants, piezobirefringence](#)
[recombination and positron lifetimes, plasmon energy](#)
[refractive and absorption index, reflectance](#)
[Seebeck coefficient](#)
[sets of Kane band parameters \(valence band parameters\)](#)
[sound velocities](#)
[spin-orbit splitting energies](#)
[thermodynamical data, vaporization](#)
[third order elastic moduli](#)
[transition pressure to \$\beta\$ -Sn structure](#)
[two-photon absorption, third order susceptibility](#)
[valence band, effective masses](#)

Silicon (Si)

[back to top](#)

[anharmonicity parameter of the LTO mode](#)
[critical point wavenumbers and phonon frequencies](#)
[elastic moduli of other Si modifications](#)
[elastic moduli of Si-I](#)
[elasto-optic \(photoelastic\) coefficients](#)
[fourth-order elastic constants of Si-I](#)
[high-frequency dielectric constant](#)
[internal strain](#)
[lattice parameters](#)
[mean square displacements](#)
[mode Grüneisen parameters](#)
[phase diagram, equation of state](#)
[phase transition pressure and volume change](#)
[phonon dispersion relations](#)
[phonon line widths and related parameters](#)
[phonon wavenumbers and frequencies](#)
[pressure dependence of elastic moduli of Si-I](#)
[pressure dependence of phonon wavenumbers and frequencies](#)
[Raman frequencies, dependence on various parameters](#)
[sound attenuation, phonon viscosity tensor](#)
[sound velocities](#)
[structure](#)
[thermal expansion](#)
[third-order elastic constants of Si-I](#)
[third-order susceptibility](#)
[Young's modulus, torsion modulus, bulk modulus](#)
[absorption index, absorption coefficient](#)
[band structure](#)
[carrier lifetimes, Auger coefficient, plasmons](#)
[conduction band, effective masses](#)
[data from Raman spectra](#)

[Debye temperature, heat capacity, density, hardness, melting point](#)
[deformation potentials](#)
[direct gap](#)
[electrical conductivity](#)
[electron drift velocity, warm electrons, intervalley relaxation time](#)
[electron mobility](#)
[energies of symmetry points of the band structure](#)
[exciton ground and related states, biexcitons](#)
[g-factor of electrons](#)
[Grüneisen parameters and related data](#)
[Hall scattering factor](#)
[higher band-band transitions \(critical point energies\)](#)
[hole drift velocity and diffusion](#)
[hole mobility](#)
[i.r. and two-photon absorption, further optical parameters](#)
[indirect energy gap](#)
[internal strain, Young's, torsion and bulk moduli](#)
[intrinsic carrier concentration](#)
[lattice parameter, thermal expansion](#)
[magnetic properties](#)
[magnetoresistance](#)
[normal and high pressure phases, liquid phase](#)
[optical constants](#)
[optical properties involving core level transitions](#)
[phonon dispersion](#)
[phonon frequencies](#)
[piezo- and elastoresistance coefficients](#)
[piezoelectric constants](#)
[plasma energy, energy loss](#)
[reflectance, dielectric constants](#)
[refractive index](#)
[Schottky barrier heights](#)
[second order elastic moduli](#)
[Seebeck and Nernst coefficients](#)
[sound velocities](#)
[spin-orbit splitting energies, second indirect gap](#)
[thermal conductivity](#)
[thermodynamical parameters](#)
[third order elastic moduli](#)
[third order susceptibilities](#)
[transport mechanism](#)
[valence band parameters](#)
[valence band, effective masses](#)

Si(x)Ge(1-x)

[electronic, lattice, transport and optical properties](#)
[thermodynamic properties](#)

[back to top](#)

Silicon carbide (SiC)

[back to top](#)

[bulk modulus, Young's modulus, shear modulus](#)
[effective charges](#)
[elastic moduli](#)
[high-frequency dielectric constant](#)
[internal strain](#)
[lattice parameters](#)
[low-frequency dielectric constant](#)
[mean square displacements](#)
[mode Grüneisen parameters](#)
[non-linear low frequency susceptibility, third-order susceptibility](#)
[phase transition pressure and volume change](#)
[phonon dispersion relations, density of states](#)
[phonon spectra, coupled phonon-plasmon modes](#)
[phonon wavenumbers and frequencies](#)
[piezoelectric and related constants](#)
[Raman phonon wavenumbers](#)
[sound velocity](#)
[structure, equation of state](#)
[thermal conductivity](#)
[thermal expansion](#)
[band structure, energy gaps](#)
[carrier concentration, resistivity, mobilities](#)
[crystal structure, unit cells, chemical bond, high pressure phases](#)
[Debye temperature, density, hardness, melting point, thermodyn. functions](#)
[dielectric constants, nonlinear optics](#)
[effective masses](#)
[electron drift velocity, breakdown field](#)
[exciton binding energy, spin-orbit splitting and interband transition energies](#)
[lattice parameters, thermal expansion](#)
[magnetic properties](#)
[mode Grüneisen parameters, sound velocity, elastic moduli, etc.](#)
[phonon dispersion, phonon frequencies and wavenumbers](#)
[polytypes](#)
[refractive index, absorption coefficient, optical spectra](#)
[thermal conductivity](#)
[valence band parameters, deformation potentials](#)
[work function](#)

Solid solutions between III-V compounds and group IV elements: (III-V)(1-x)IV(x,2x)

[data](#)

[back to top](#)

Solid solutions between III-V and II-VI compounds: (III-V)(x)(II-VI)(1-x)

[comparative table](#)

[back to top](#)

Lattice Properties

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